

FileViewEditToolsWindowHelp

Drafts

Pending

Active

Failed

Saved

Favorites

Tagged (3)

UDC

Queue

Trash

L1: (16) (MRAM (magnetic near4 memory)) and ((magnet\$2 near3 tunnel\$3 near3 junction) with source...

L2: (47) (MRAM (magnetic near4 memory)) and ((MTJ (magnet\$2 near3 tunnel\$3 near3 junction)) with source) and ((MTJ (magnet\$2 near3 tunnel\$3 near3 junction)) with gate)

L3: (4736) MTJ (magnet\$2 near3 tunnel\$3 near3 junction) TMR (tunnel\$3 near3 magnet\$2 near3 resist\$3)

L4: (62) (MRAM (magnetic near4 memory)) and (L3 with source) and (L3 with gate)

DB: USPAT, US POPUS, EPO, JPO, DERWENT, IBM, TDB

Back

Highlight all items with...

40517) MRAM (magnetic near4 memory)

(3376) (MRAM (magnetic near4 memory)) and ((magnet\$2 ferromagnet\$2) adj2 layer)

(996) magnet\$2 near3 tunnel\$3 near3 junction

(517) ((MRAM (magnetic near4 memory)) and ((magnet\$2 ferromagnet\$2) adj2 layer))

(10) ((MRAM (magnetic near4 memory)) and ((magnet\$2 ferromagnet\$2) adj2 layer))

(0) (MRAM (magnetic near4 memory)) and ((magnet\$2 adj2 tunnel\$3) near3 source) and

(1) (MRAM (magnetic near4 memory)) and ((magnet\$2 near3 tunnel\$3 near3 junction)

(0) (MRAM (magnetic near4 memory)) and ((junction adj3 end) near3 gate) and ((jun

(4411) mizushima.in.

(173) (mizushima near koichi).in.

(26) ((mizushima near koichi).in.) and magnetic

(26) ((mizushima near koichi).in.) and magnet\$3

4 BRS form

4 BRS form

Image

Text

HTML

	Type	L #	Hits	Search Text	DBs	Time Stamp	C
1	BRS	L1	16	(MRAM (magnetic near4 memory)) and ((magnet\$2 near3 tunnel\$3 near3 junction) with source) and ((magnet\$2 near3 tunnel\$3 near3 junction) with gate)	USPAT	2004/01/15 13:22	
2	BRS	L2	47	(MRAM (magnetic near4 memory)) and ((MTJ (magnet\$2 near3 tunnel\$3 near3 junction)) with source) and ((MTJ (magnet\$2 near3 tunnel\$3 near3 junction)) with gate)	USPAT	2004/01/15 13:19	
3	BRS	L3	4736	MTJ (magnet\$2 near3 tunnel\$3 near3 junction) TMR (tunnel\$3 near3 magnet\$2 near3 resist\$3)	USPAT	2004/01/15 13:21	
4	BRS	L4	62	(MRAM (magnetic near4 memory)) and (L3 with source) and (L3 with gate)	USPAT	2004/01/15 13:22	

Ready

NUM

EAST - [10079116.wsp:1]

File View Edit Tools Window Help

Drafts

Pending

Active

Failed

Saved

Favorites

Tagged (3)

UDC

Queue

Trash

L1: (16) (MRAM (magnetic near4 memory)) and ((magnet\$2 near3 tunnel\$3 near3 junction))

L2: (47) (MRAM (magnetic near4 memory)) and ((MTJ (magnet\$2 near3 tunnel\$3 near3 junction))

L3: (4736) MTJ (magnet\$2 near3 tunnel\$3 near3 junction) TMR (tunnel\$3 near3 junction)

L4: (62) (MRAM (magnetic near4 memory)) and (L3 with source) and (L3 with gate)

Browser Queue Draw

DB: USPAT:USPGFUB:EPO:JPO:DERWENT:HM:TOP

Draw

DETAIL operator: CR

Highlight all terms in body

(MRAM (magnetic near4 memory)) and (L3 with source) and (L3 with gate)

US 20040008556 20040115 33 Memory device reading data according to difference in 365/210 365/158; 365/173 Hidaka, Hideto

US 20030227799 20031211 13 Tunnel magnetoresistive effect element, method of 365/200 Higo, Yutaka et al.

US 20030223203 20031204 71 Magnetic memory device 365/200 Kunikiyo, Tatsuya

US 20030218901 20031127 41 Thin film magnetic memory device having an access 365/157 Ooishi, Tsukasa et al.

US 20030214839 20031120 7 Magnetic random access memory 365/173 Jang, In Woo et al.

US 20030202407 20031030 40 MEMORY DEVICE HAVING WIDE MARGIN OF DATA READING 365/200 Hidaka, Hideto

US 20030198080 20031023 200 Magnetic random access memory 365/158 Iwata, Yoshihisa

Ready

NUM